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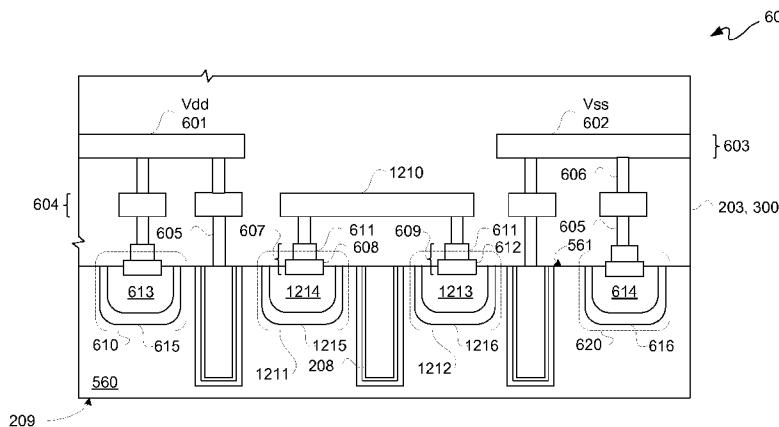


FIG. 12

(57) Abstract: An apparatus relating generally to an interposer (600, 700, 800) is disclosed. In such an apparatus, the interposer (600, 700, 800) has a plurality of conductors (208, 451-459, 603-606) and a plurality of charge attracting structures (610, 620, 710, 720, 810, 820). The plurality of charge attracting structures (610, 620, 710, 720, 810, 820) are to protect at least one integrated circuit die (202) to be coupled to the interposer (600, 700, 800) to provide a stacked die (200). The plurality of conductors (208, 451-459, 603-606) include a plurality of through-substrate vias (208).